IXYS

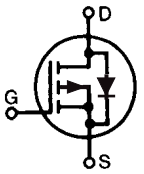
Preliminary Technical Information

TrenchP™ Power MOSFETs

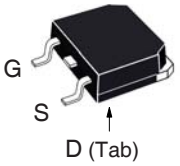
IXTT68P20T
IXTH68P20T

V_{DSS} = - 200V
I_{D25} = - 68A
$R_{DS(on)}$ ≤ 55mΩ

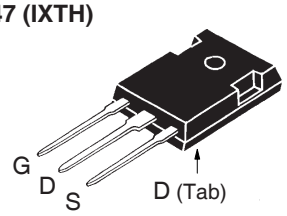
P-Channel Enhancement Mode
Avalanche Rated



TO-268 (IXTT)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	- 200	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	- 200	V
V_{GSS}	Continuous	±15	V
V_{GSM}	Transient	±25	V
I_{D25}	T_C = 25°C	- 68	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	- 200	A
I_A	T_C = 25°C	- 68	A
E_{AS}	T_C = 25°C	2.5	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	10	V/ns
P_D	T_C = 25°C	568	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-268	4	g
	TO-247	6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = - 250μA	- 200			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250μA	- 2.0		- 4.0	V
I_{GSS}	V_{GS} = ±15V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			- 10	μA
	T_J = 125°C			- 200	μA
$R_{DS(on)}$	V_{GS} = -10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			55	mΩ

Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low $R_{DS(ON)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = -10V, I_D = 0.5 • I_{D25}, Note 1	55	90		S
C_{iss}	V_{GS} = 0V, V_{DS} = - 25V, f = 1MHz		33.4		nF
C_{oss}			1300		pF
C_{rss}			307		pF
$t_{d(on)}$	**Resistive Switching Times**		63		ns
t_r	V_{GS} = -10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		29		ns
$t_{d(off)}$	R_G = 1Ω (External)		115		ns
t_f			18		ns
$Q_{g(on)}$	V_{GS} = -10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		380		nC
Q_{gs}			125		nC
Q_{gd}			70		nC
R_{thJC}				0.22	°C/W
R_{thCS}	TO-247		0.21		°C/W

Source-Drain Diode

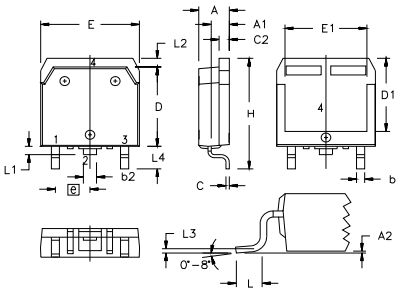
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			- 68	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			- 270	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			-1.4	V
t_{rr}	I_F = - 34A, -di/dt = -100A/μs		245		ns
Q_{RM}	V_R = -100V, V_{GS} = 0V		2.6		μC
I_{RM}			- 21.4		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

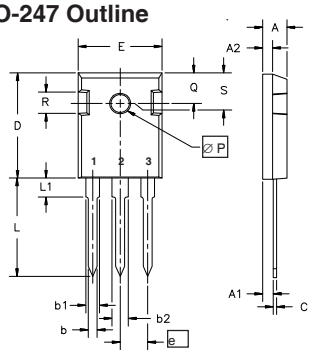
TO-268 Outline



Terminals: 1 - Gate 2,4 - Drain
3 - Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

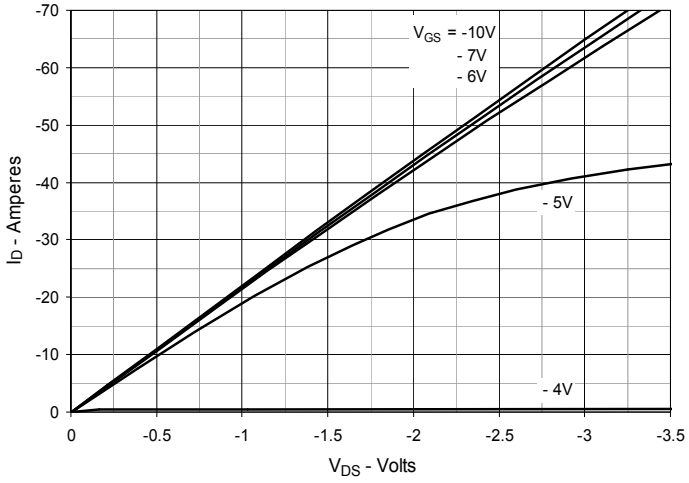


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

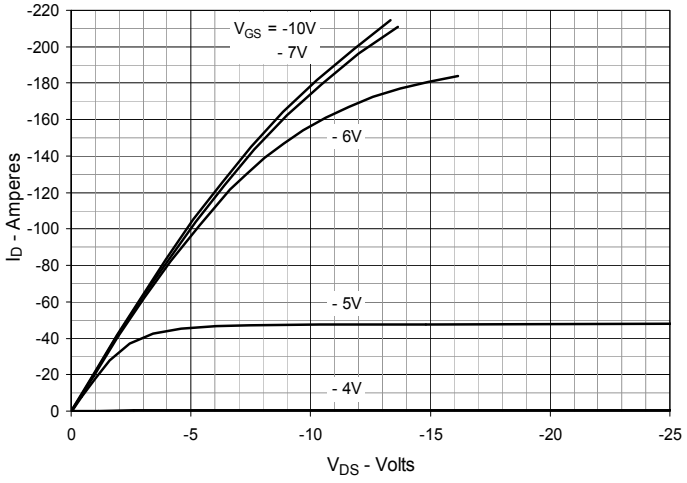


Fig. 3. Output Characteristics @ T_J = 125ºC

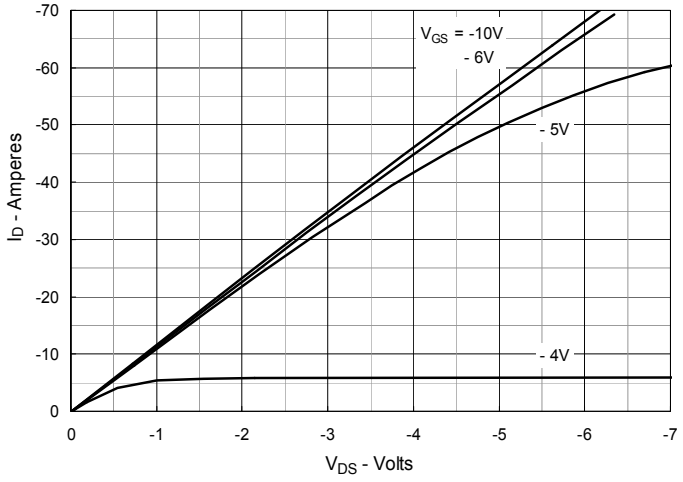


Fig. 4. $R_{DS(on)}$ Normalized to I_D = - 34A Value vs. Junction Temperature

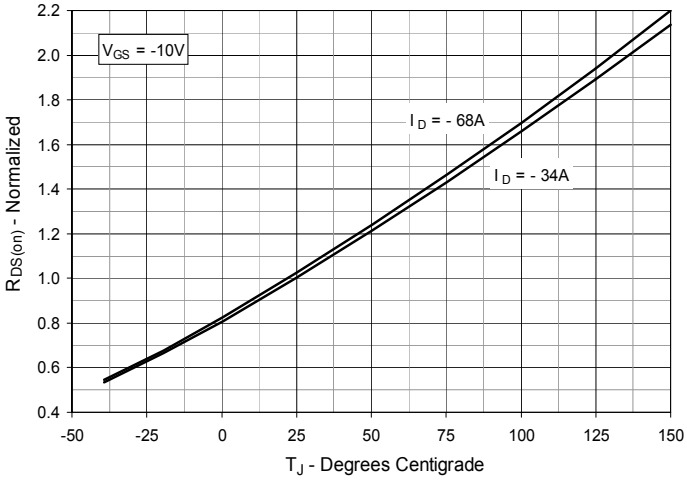


Fig. 5. $R_{DS(on)}$ Normalized to I_D = - 34A Value vs. Drain Current

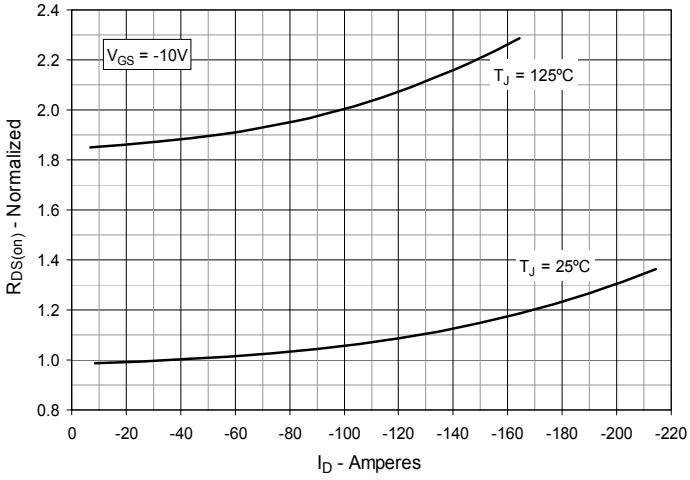
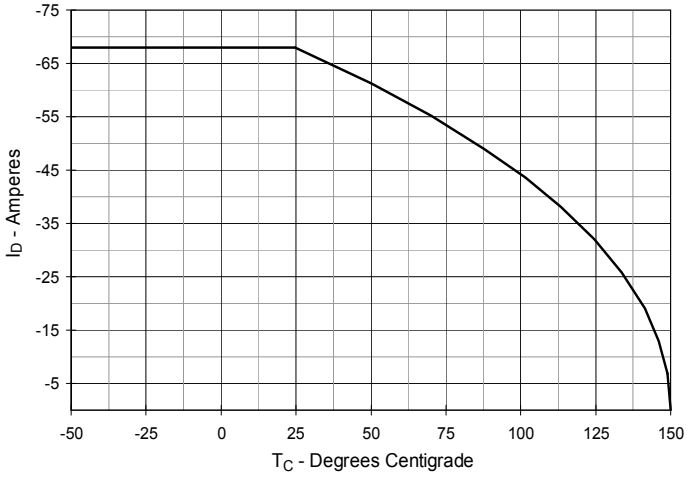


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

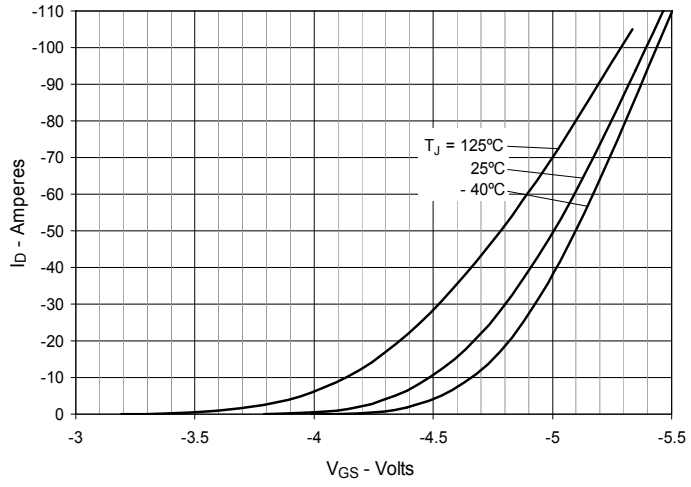


Fig. 8. Transconductance

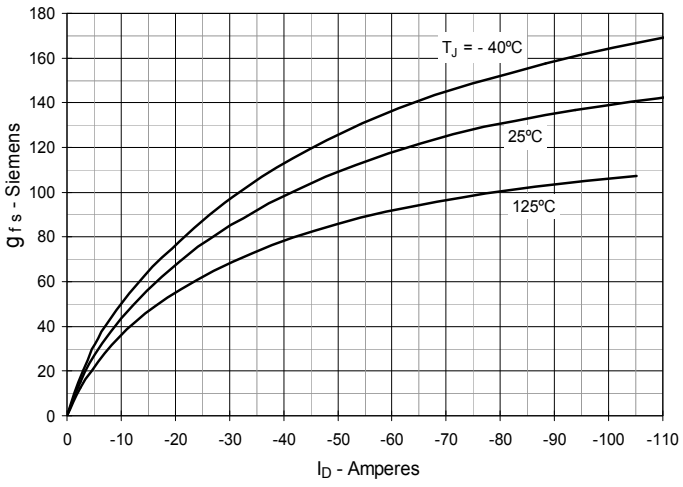


Fig. 9. Forward Voltage Drop of Intrinsic Diode

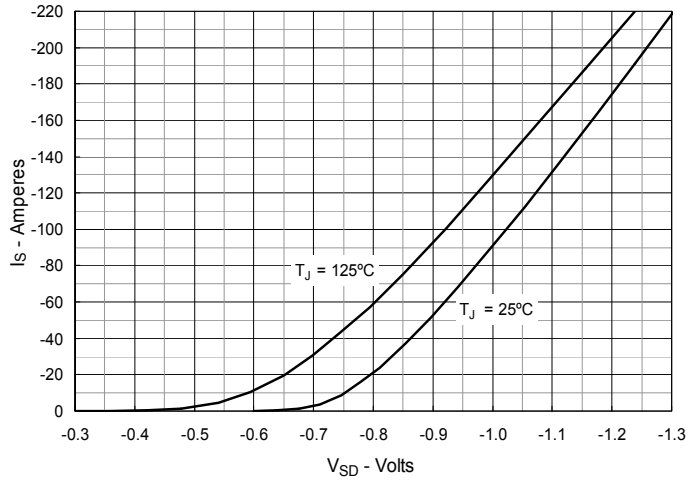


Fig. 10. Gate Charge

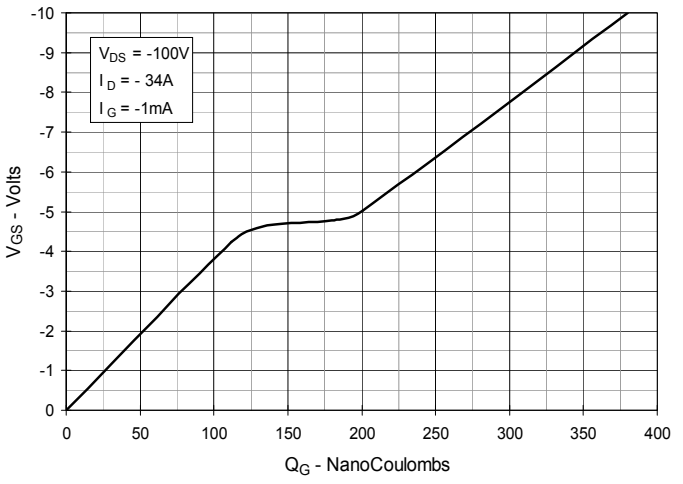


Fig. 11. Capacitance

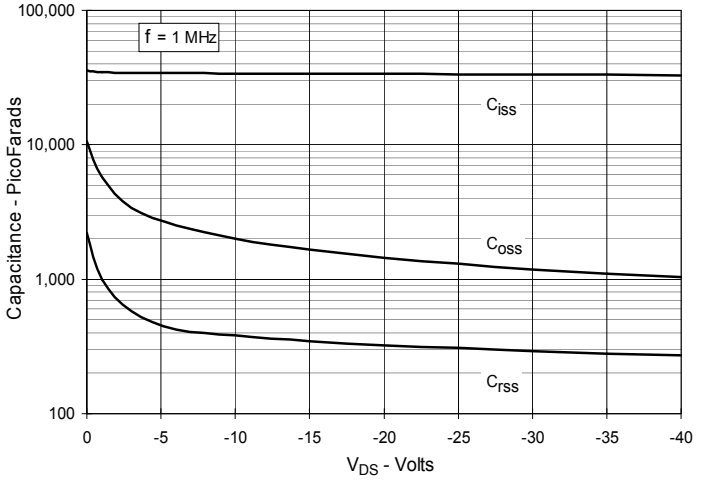
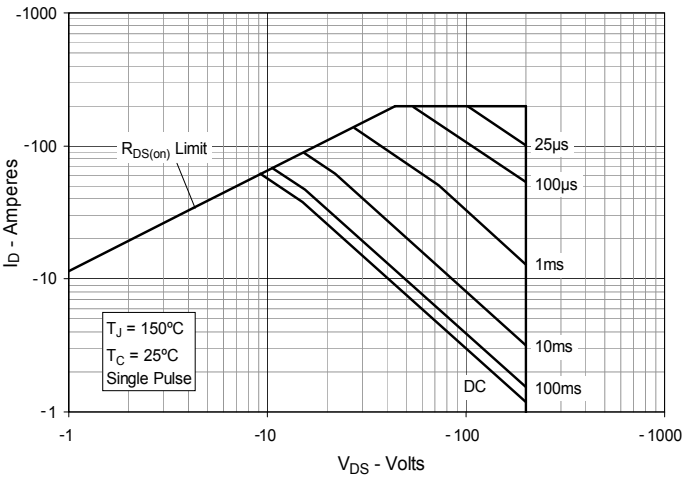


Fig. 12. Forward-Bias Safe Operating Area



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

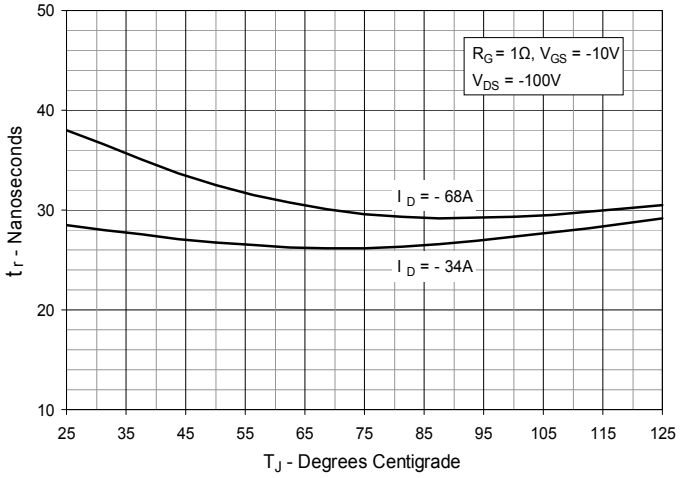


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

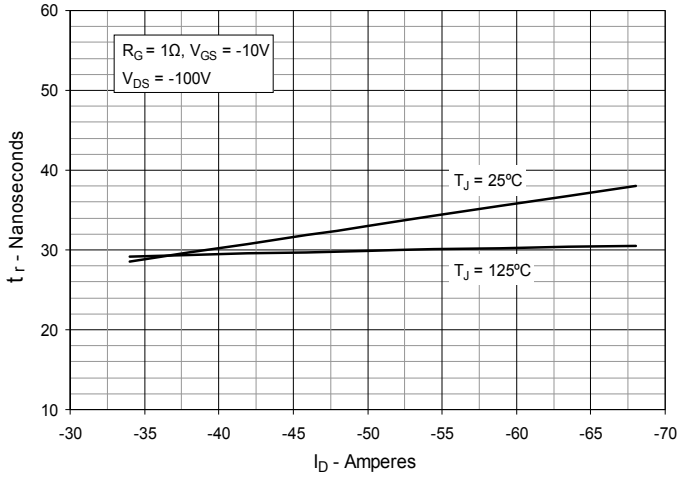


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

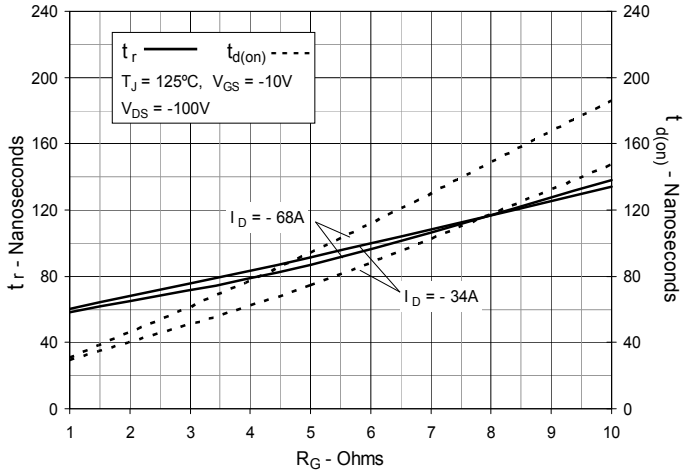


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

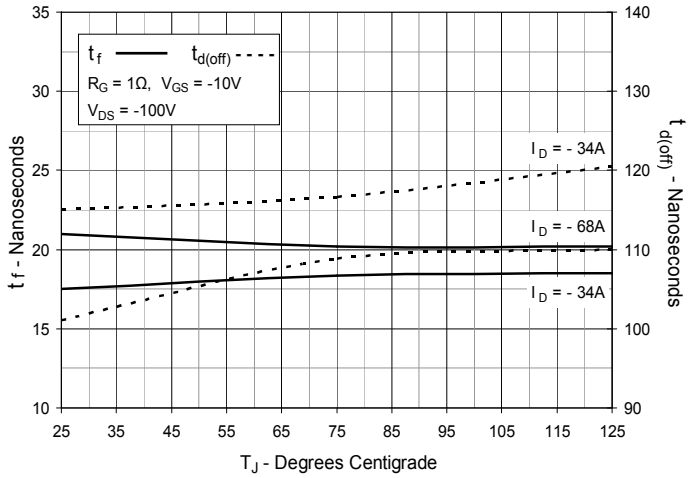


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

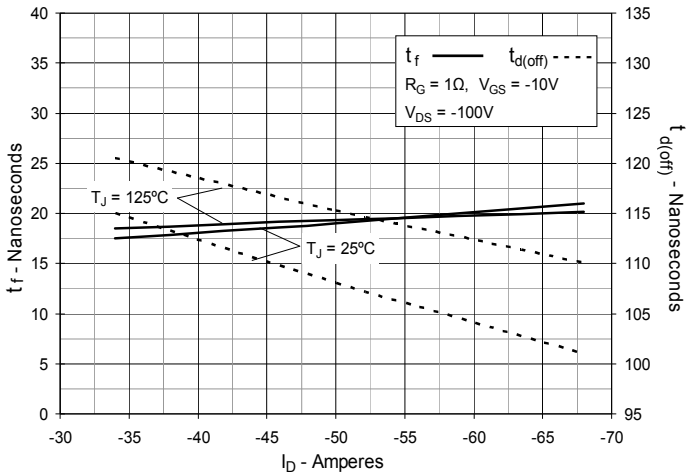
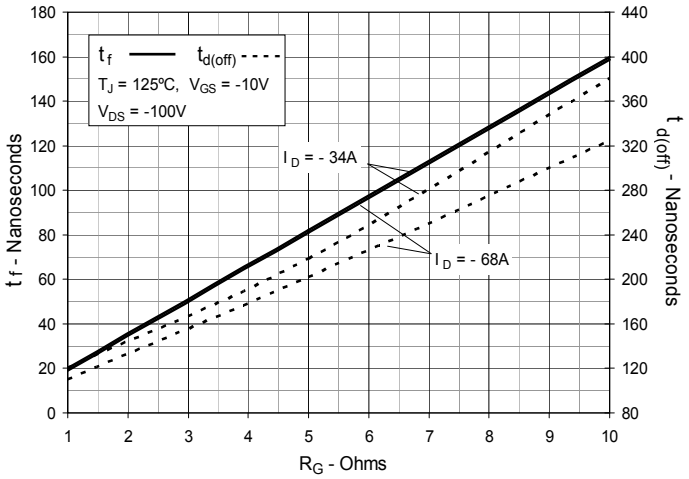


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance



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Fig. 19. Maximum Transient Thermal Impedance

